

Erratum

Correction to "A Comparative Analysis of Substrate Current Generation Mechanisms in Tunneling MOS Capacitors"

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In the above paper,¹ an incorrect version of Fig. 5 appeared, due to a production error. The correct figure is shown as follows.

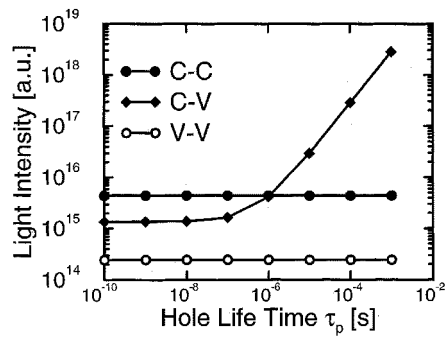


Fig. 5. Contribution of C-C, C-V, and V-V transitions to the total light intensity emitted inside the gate, as a function of the minority life time, for a nMOS capacitor with $t_{OX} = 5.5$ nm and $V_G = 8$ V. All photons with $E_{ph} > E_G$ were considered.

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¹P. Palestri, A. Della Serra, L. Selmi, M. Pavesi, P. L. Rigolli, A. Abramo, F. Widdershoven, and E. Sangiorgi, *IEEE Electron Devices*, vol. 49, pp. 1427–1435, August 2002.